

### General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is ideal for load switch and battery protection applications.

### Features

cell density Trench technology  
 $R_{DS(ON)}$  to minimize conductive loss

### Product Summary

### Application

nd Synchronous Rectifier

### Ordering Information:

	TUBE
	1000

### Absolute Maximum Ratings $T_C=25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D @ T_C=25$	178	A
	$I_D @ T_C=75$	135	A
	$I_D @ T_C=100$	112	A
Pulsed Drain Current	$I_{DM}$	534	A
Total Power Dissipation	$P_D @ T_C=25$	113	W
Total Power Dissipation	$P_D @ T_A=25$	3.2	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	
Single Pulse Avalanche Energy	$E_{AS}$	210	mJ







Fig.13 Resistive Switching Test Circuit

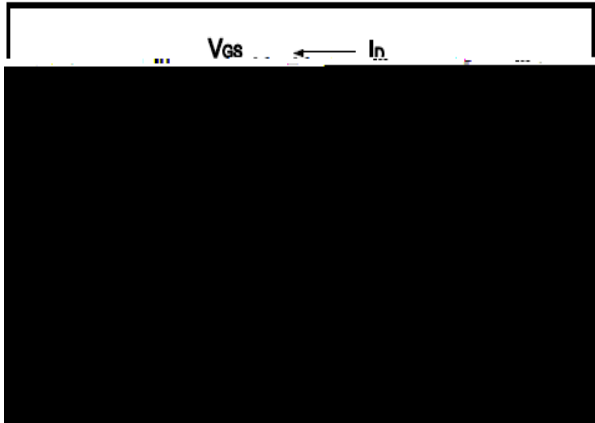


Fig.14 Resistive Switching Test Waveform

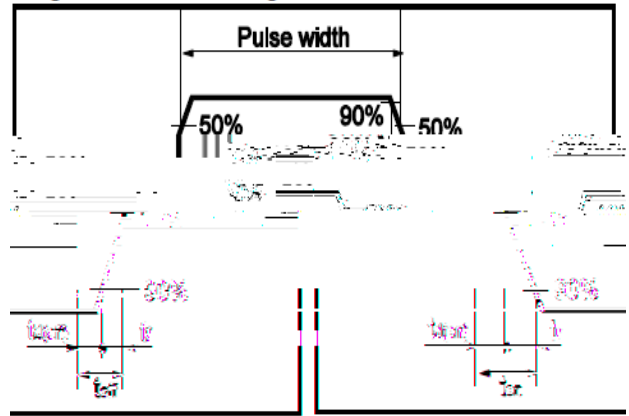


Fig.15 Avalanche Measurement Circuit

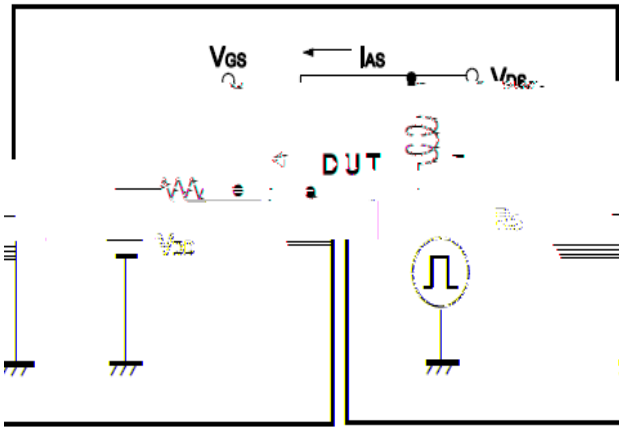
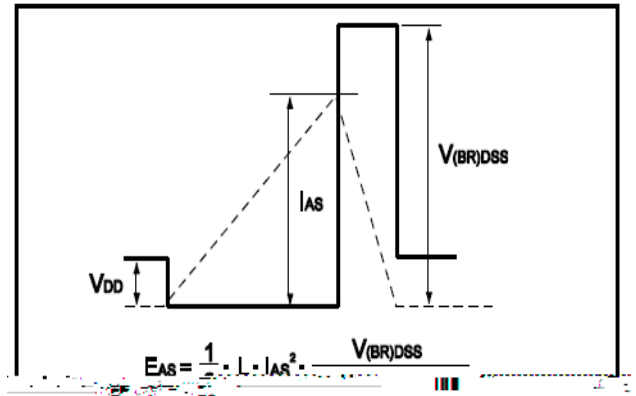


Fig.16 Avalanche Waveform





Dimensions (TO-220)

Unit mm

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	.		.		0..		1..
					1 .		1 .

